TOSHIBA Intelligent Power Module Silicon N Channel IGBT

MIG300Q101H

High Power Switching Applications Motor Control Applications

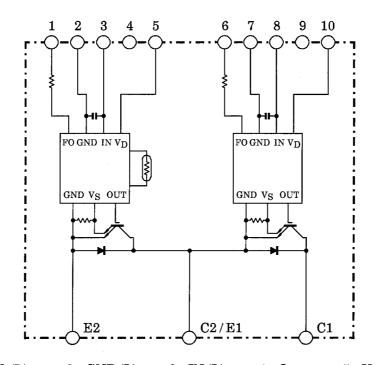
• Integrates inverter power circuits & control circuits (IGBT drive units, protection units for over-current, under-voltage & over temperature) in one package.

The electrodes are isolated from case.

Outline : TOSHIBA 2-121A1A

Weight : 510g

Equivalent Circuit



- 1. FO(L)
- 2. GND (L)
- 3. IN(L)
- 4. Open
- 5. $V_D(L)$

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Maximum Ratings $(T_j = 25^{\circ}C)$

Stage	Characteristic	Condition	Symbol	Ratings	Unit
Inverter	Supply voltage	P-N power terminal	V _{CC}	900	V
	Collector-emitter voltage	_	V _{CES}	1200	V
	Collector current	Tc = 25°C, DC	Ic	300	Α
	Forward current	Tc = 25°C, DC	l _F	300	Α
	Collector power dissipation	Tc = 25°C	PC	1600	W
	Junction temperature	_	Tj	150	°C
Control	Control supply voltage	V _D -GND terminal	V _D	20	V
	Input voltage	IN-GND terminal	V _{IN}	20	V
	Fault output voltage	FO-GND (L) terminal	V _{FO}	20	V
	Fault output current	FO sink current	I _{FO}	14	mA
Module	Operating temperature	_	T _C	-20~+100	°C
	Storage temperature range	_	T _{stg}	-40~+125	°C
	Isolation voltage	AC 1 minute,	V _{ISO}	2500	V
	Screw torque	M6	_	3	N·m

Electrical Characteristics ($T_j = 25$ °C)

a. Inverter Stage

Characteristic	Symbol	Test Condition		Min	Тур.	Ма.	Unit
Collector cut-off current	I _{CEX} V _{CE} = 1200V	Voc = 1200V	T _j = 25°C	_	_	2	- mA
Conector cut-on current		VCE - 1200V	T _j = 125°C	_	_	40	
Collector-emitter saturation voltage		V _D = 15V, I _C = 300A	T _j = 25°C	_	2.7	2.5	V
Conector-emitter saturation voltage		V _{IN} = 3V→0V	T _j = 125°C	_	2.6	_	
Forward voltage	V _F	I _F = 300A		_	2.0	3.0	V
	t _{on}	V_{CC} = 600V, I_{C} = 300A V_{D} = 15V, V_{IN} = 3V \leftrightarrow 0V Inductive load		0.8	1.5	2.2	μs
	t _{c (on)}			_	0.5	1.0	
Switching time	t _{rr}			_	0.2	0.3	
	t _{off}		(Note 1)		3.3	3.8	
	t _{c (off)}			_	0.4	0.8	

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b. Control Stage $(T_j = 25^{\circ}C)$

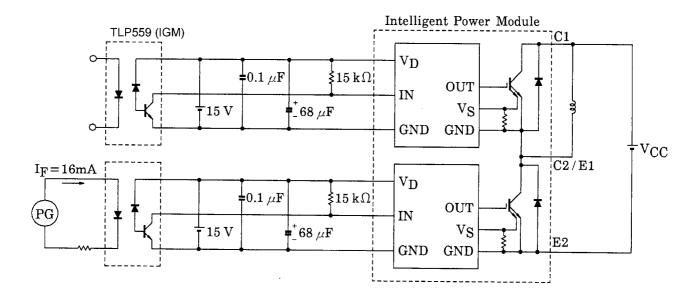
Characteristic		Symbol	Test Condition	Min	Тур.	Max	Unit
Control circuit current		I _D	V _D = 15V	_	20	30	mA
Input on signal voltage		V _{IN (on)}	V _D = 15V, I _C = 300mA	0.9	1.1	1.3	V
Fault output current	Protection	I _{FO (on)}	- V _D = 15V	8	10	12	mA
	Normal	I _{FO (off)}		_	_	1	
Over current protection trip level		ОС	V _D = 15V, T _j = 125°C	420	600	_	Α
Short circuit protection trip level		SC	V _D = 15V, T _j = 125°C	630	900	_	Α
Over current cut-off time		t _{off (OC)}	V _D = 15V	_	10	_	μs
Over	Trip level	ОТ	Case temperature	111	118	125	°C
temperature protection	Reset level	OTr		_	100	_	
Control supply	Trip level	UV		11.3	12.0	12.7	V
under voltage protection	Reset level	UVr	_	11.8	12.5	13.2	
Fault output pulse width		t _{FO}	V _D = 15V	1	2	3	ms

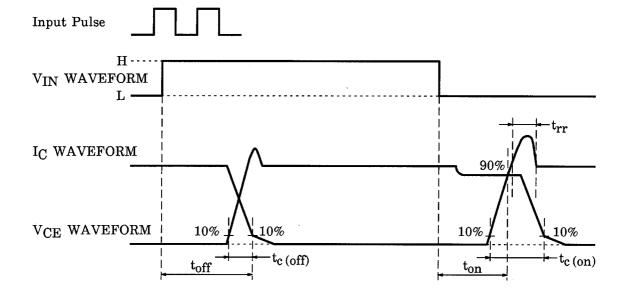
c. Thermal Resistance $(T_j = 25^{\circ}C)$

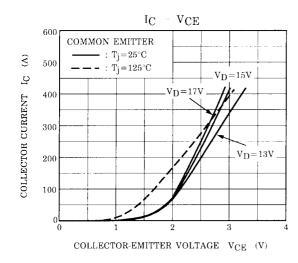
Characteristic	Symbol	Test Condition	Min	Тур.	Max	Unit
Junction to case thermal	R _{th (j-c)}	IGBT	_	_	0.078	°C/W
resistance	FR	FRD	_	_	0.25	
Case to fin thermal resistance	R _{th (c-f)}	Compound is applied	_	0.05	_	°C/W

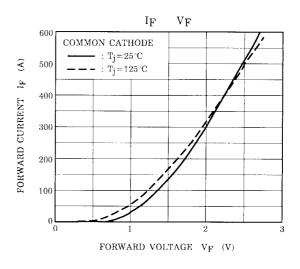
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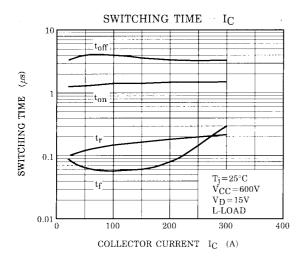
Note 1: Switching time test circuit & timing chart

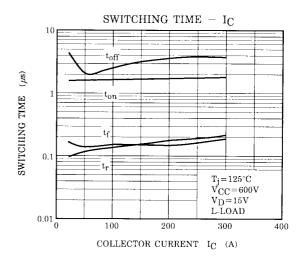


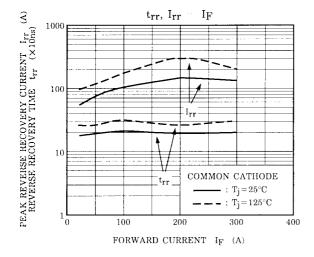


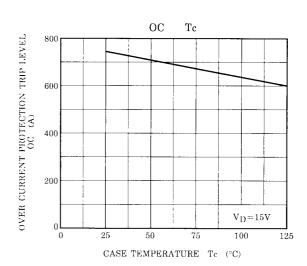




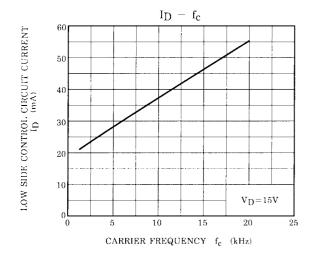


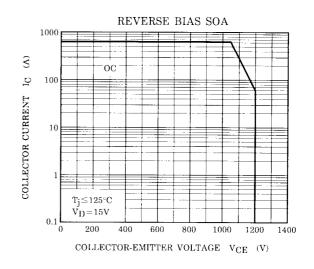


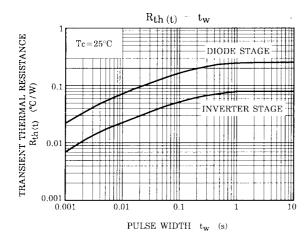




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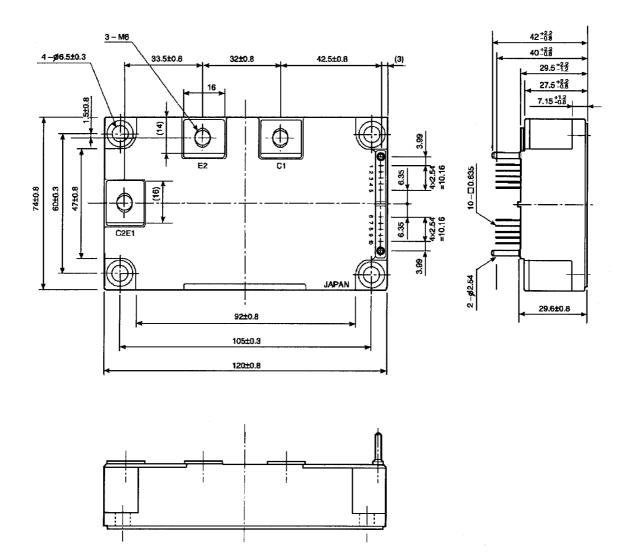




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Package Dimensions: TOSHIBA 2-121A1A

Unit: mm



- 1. FO(L)
- 2. GND (L) 3. IN (L)
- 4. Open

- 6. FO(H)
- 7. GND(H) 8. IN(H)
- 9. Open
- $\begin{array}{cc} 5. & V_{D}\left(L\right) \\ 10. V_{D}\left(H\right) \end{array}$

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